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FGD5T120SH

1200 V, 5 A FS Trench IGBT

Features

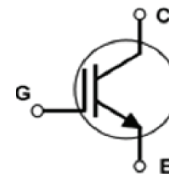
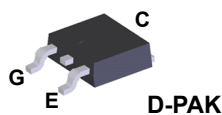
- FS Trench Technology, Positive Temperature Coefficient
- High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)} = 2.9 \text{ V @ } I_C = 5 \text{ A}$
- 100% of the Parts tested for $I_{LM}(1)$
- High Input Impedance
- RoHS Compliant

Applications

- Inrush current limitation
- Lighting
- Home appliances

General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 3rd generation IGBTs offer the optimum performance for inrush current limitation, lighting and home appliance applications.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FGD5T120SH	Unit
V_{CES}	Collector to Emitter Voltage	1200	V
V_{GES}	Gate to Emitter Voltage	± 25	V
	Transient Gate to Emitter Voltage	± 30	V
I_C	Collector Current	@ $T_C = 25^\circ\text{C}$	10
	Collector Current	@ $T_C = 100^\circ\text{C}$	5
$I_{LM} (1)$	Clamped Inductive Load Current	@ $T_C = 25^\circ\text{C}$	12.5
$I_{CM} (2)$	Pulsed Collector Current		12.5
P_D	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	69
	Maximum Power Dissipation	@ $T_C = 100^\circ\text{C}$	28
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

- Notes:**
 1. $V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 12.5 \text{ A}, R_G = 50 \Omega$, Inductive Load
 2. Limited by T_{jmax}

Thermal Characteristics

Symbol	Parameter	FGD5T120SH	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	1.8	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (3)	50	$^{\circ}\text{C}/\text{W}$

Notes : 3. Mounted on 1" square PCB (FR4 or G-10 material)

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Qty per Tube
FGD5T120SH	FGD5T120SH	TO-252 A03	380 mm	16 mm	2500

Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	1200	-	-	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	-	1.2	-	$\text{V}/^{\circ}\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 5\text{ mA}, V_{CE} = V_{GE}$	2.5	3.5	4.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 5\text{ A}, V_{GE} = 15\text{ V}$	-	2.9	3.6	V
		$I_C = 5\text{ A}, V_{GE} = 15\text{ V}, T_C = 150^{\circ}\text{C}$	-	4.5	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	209	-	pF
C_{oes}	Output Capacitance		-	11	-	pF
C_{res}	Reverse Transfer Capacitance		-	2	-	pF
Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{ V}, I_C = 5\text{ A}, R_G = 30\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 25^{\circ}\text{C}$	-	4.8	-	ns
T_r	Rise Time		-	20.8	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	24.8	-	ns
T_f	Fall Time		-	104	-	ns
E_{on}	Turn-On Switching Loss		-	247	-	μJ
E_{off}	Turn-Off Switching Loss		-	94	-	μJ
E_{ts}	Total Switching Loss		-	341	-	μJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{ V}, I_C = 5\text{ A}, R_G = 30\text{ }\Omega, V_{GE} = 15\text{ V}, \text{Inductive Load}, T_C = 150^{\circ}\text{C}$	-	4.8	-	ns
T_r	Rise Time		-	40	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	25.6	-	ns
T_f	Fall Time		-	134	-	ns
E_{on}	Turn-On Switching Loss		-	393	-	μJ
E_{off}	Turn-Off Switching Loss		-	114	-	μJ
E_{ts}	Total Switching Loss		-	507	-	μJ
Q_g	Total Gate Charge	$V_{CC} = 600\text{ V}, I_C = 5\text{ A}, V_{GE} = 15\text{ V}$	-	6.7	-	nC
Q_{ge}	Gate to Emitter Charge		-	1.8	-	nC
Q_{gc}	Gate to Emitter Charge		-	2.6	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

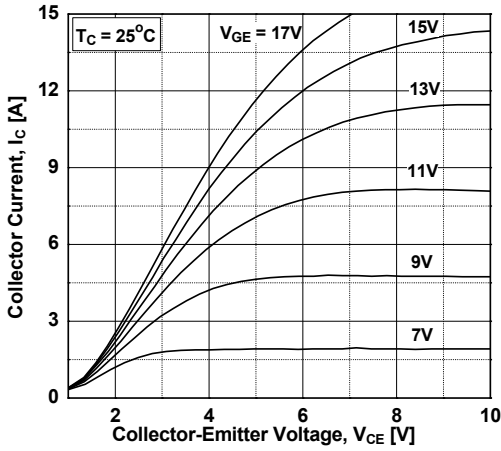


Figure 2. Typical Output Characteristics

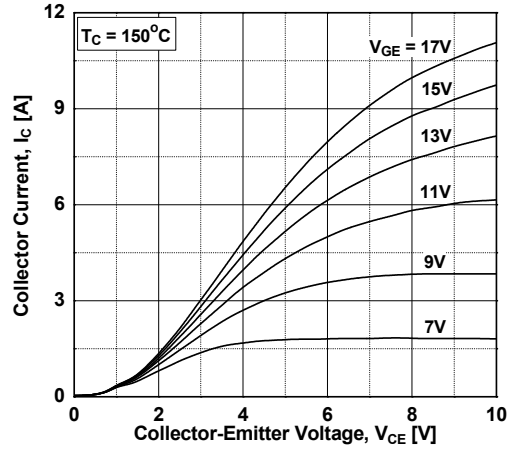


Figure 3. Typical Saturation Voltage Characteristics

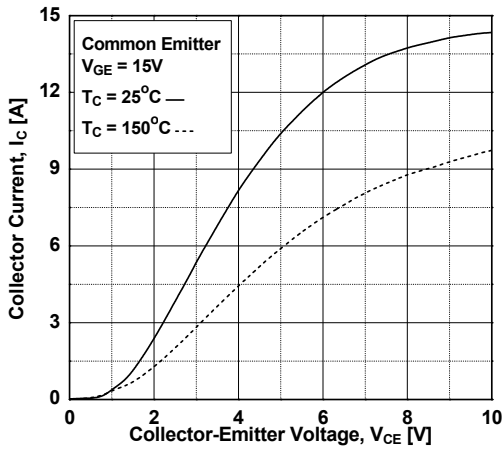


Figure 4. Transfer Characteristics

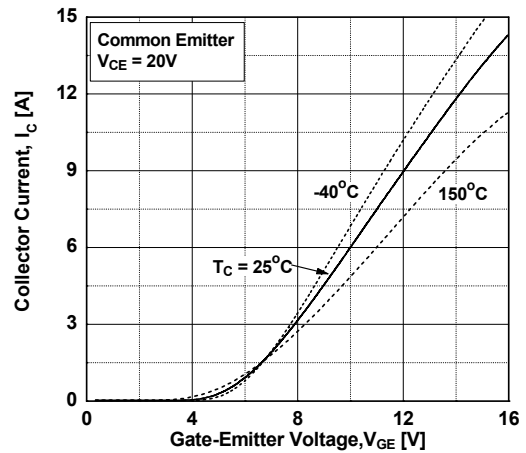


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

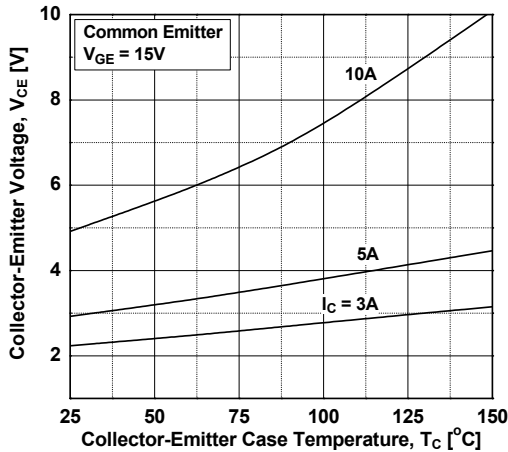
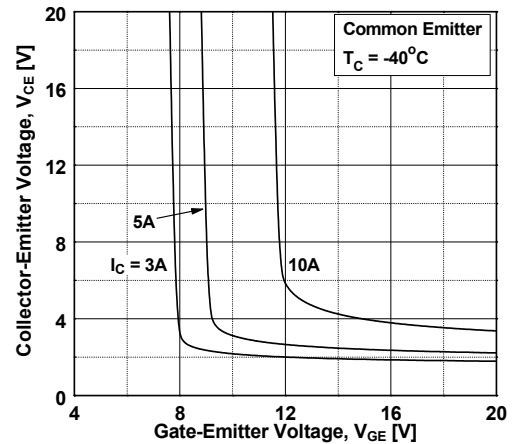


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

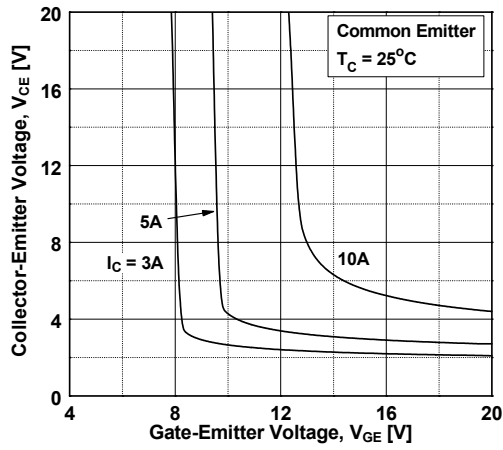


Figure 8. Saturation Voltage vs. V_{GE}

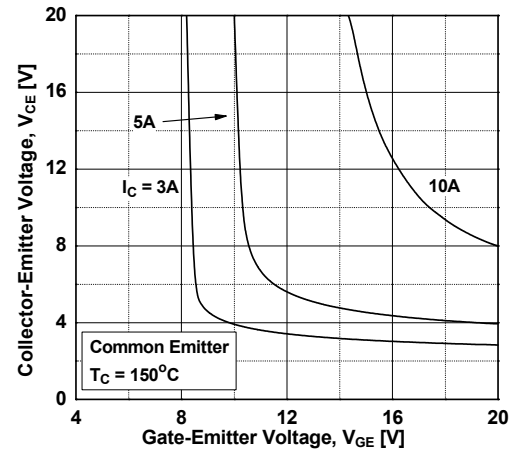


Figure 9. Capacitance Characteristics

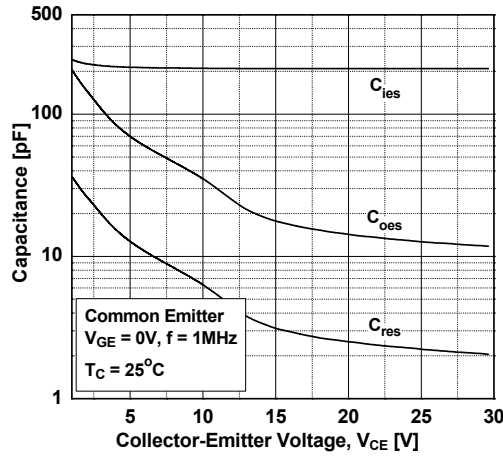


Figure 10. Gate Charge Characteristics

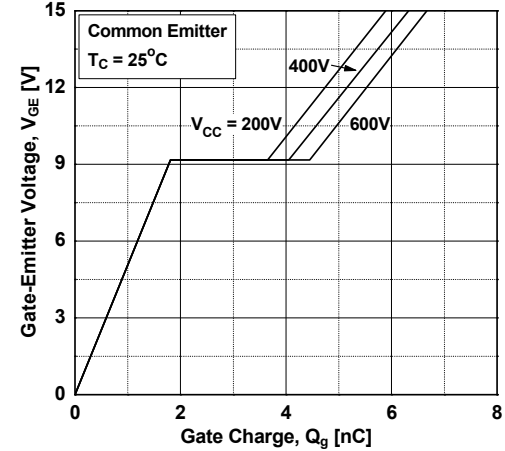


Figure 11. SOA Characteristics

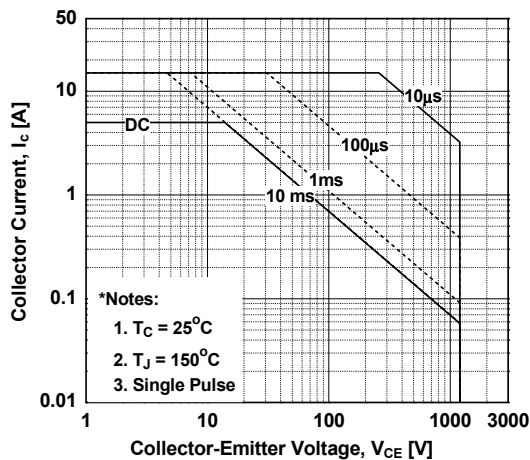
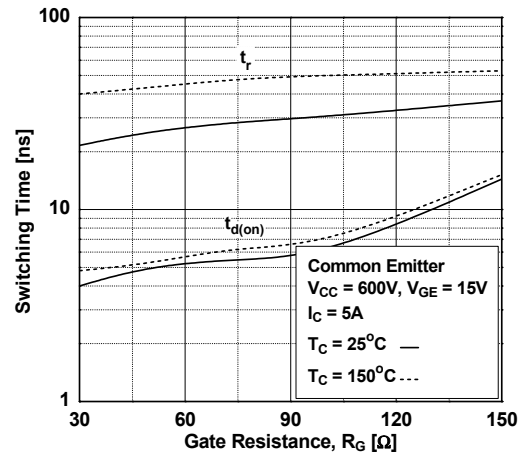


Figure 12. Turn-on Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-off Characteristics VS. Gate Resistance

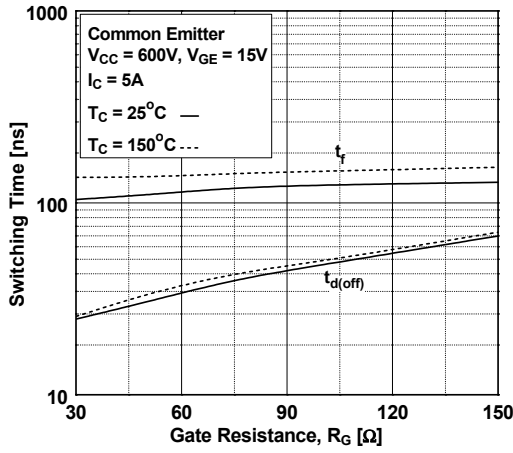


Figure 14. Turn-on Characteristics VS. Collector Current

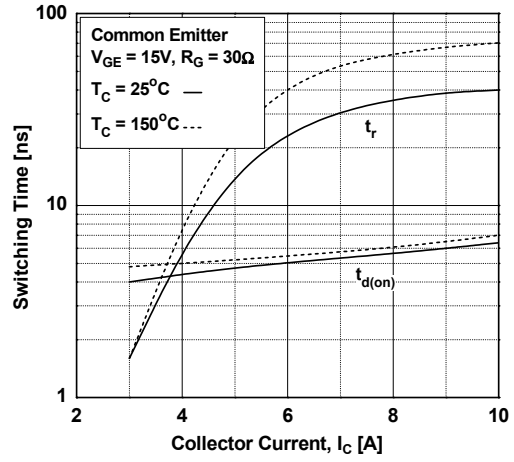


Figure 15. Turn-off Characteristics VS. Collector Current

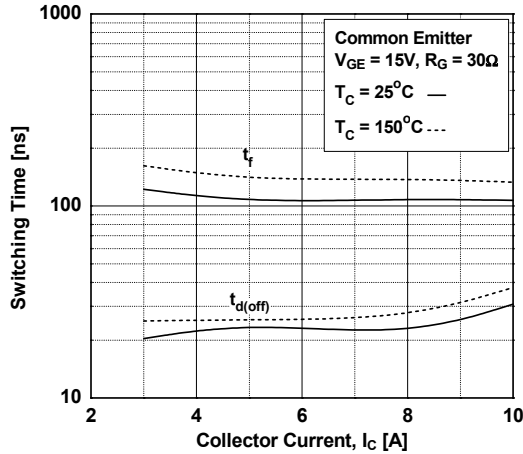


Figure 16. Switching Loss VS. Gate Resistance

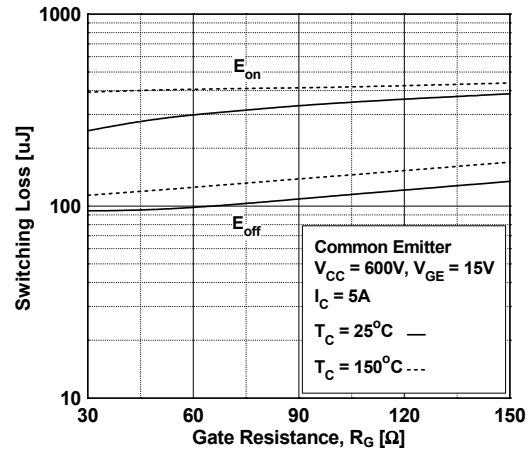


Figure 17. Switching Loss VS. Collector Current

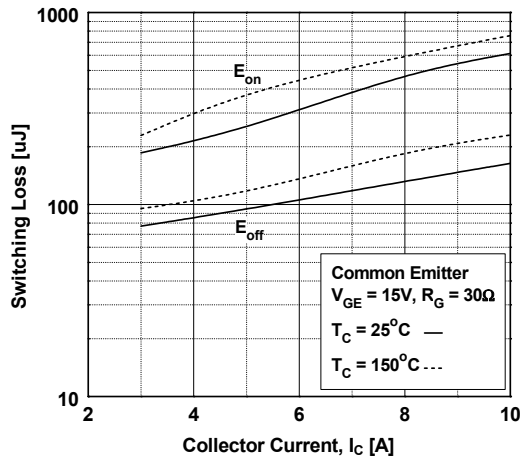


Figure 18. Current Derating

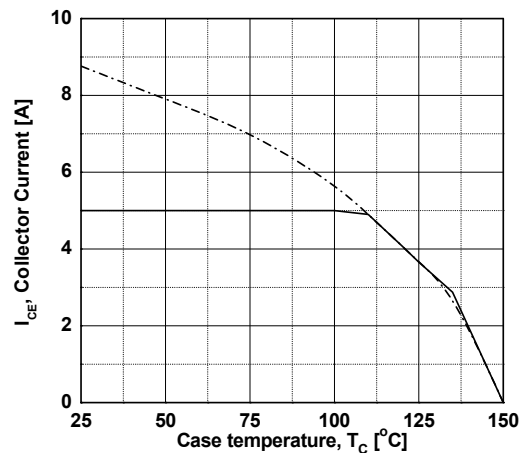


Figure 19. Load Current Vs. Frequency

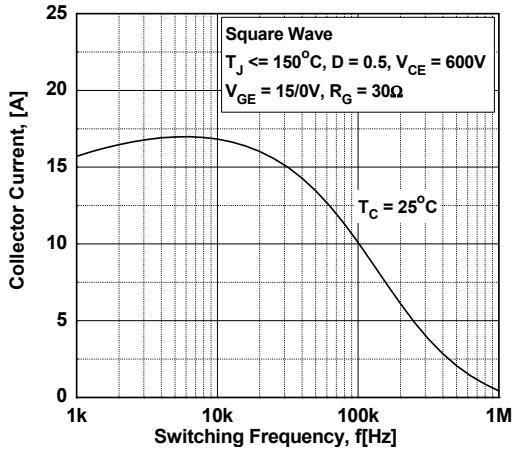
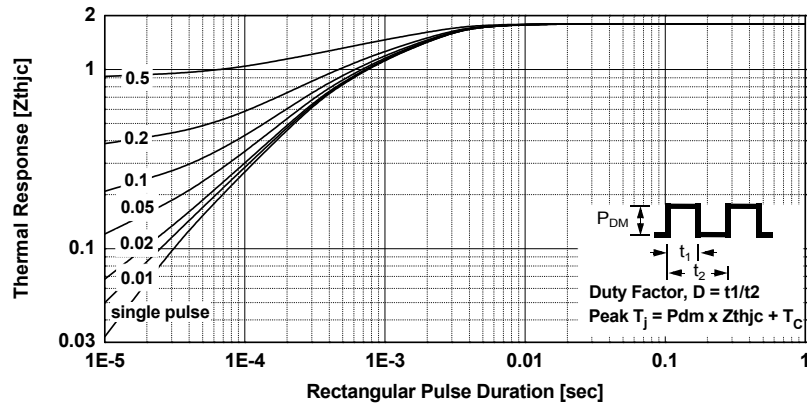


Figure 20. Transient Thermal Impedance of IGBT



Mechanical dimensions

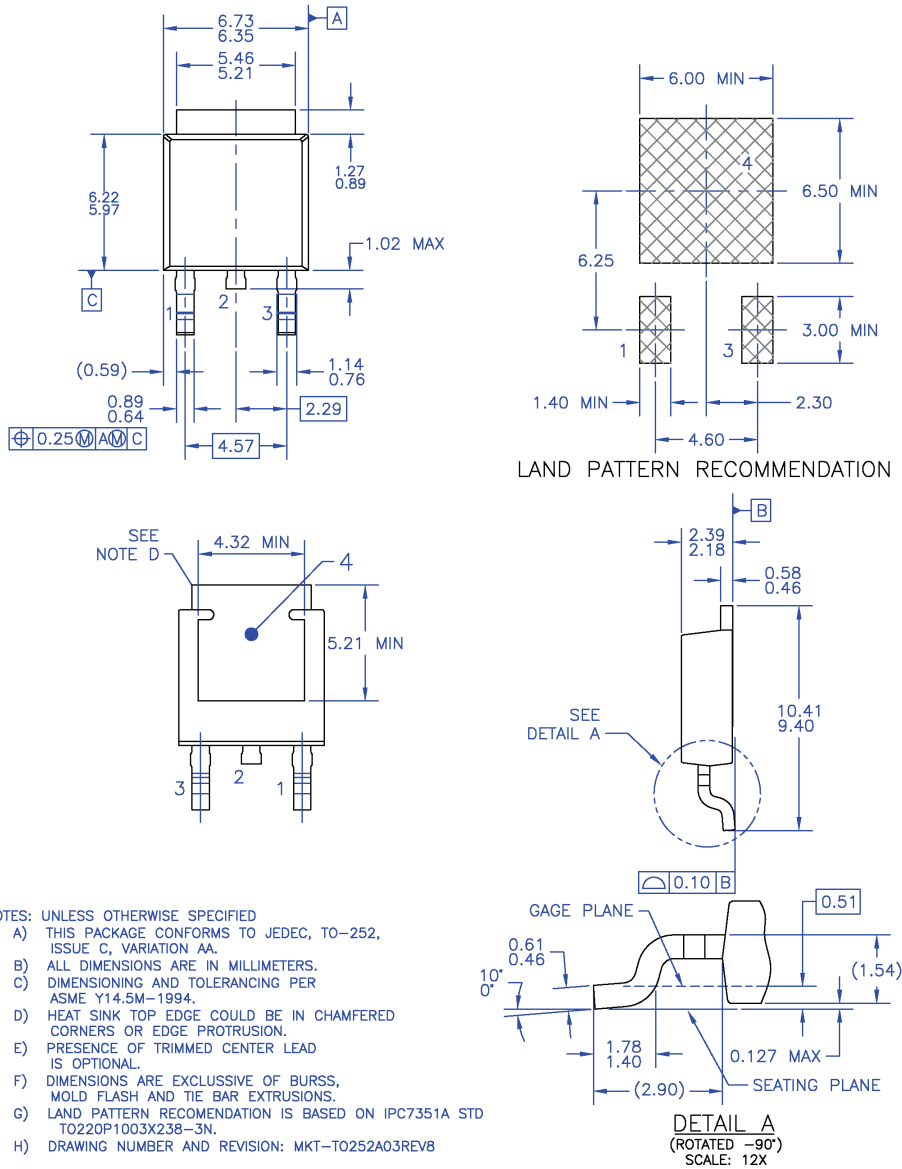


Figure 21. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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